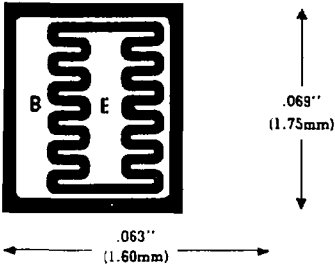


CHIP NUMBER

269



Base: .009" x .050" (0.23mm x 1.27mm)  
Emitter: .009" x .042" (0.23mm x 1.07mm)

**PNP EPITAXIAL PLANAR POWER TRANSISTOR\*\* (FORMERLY 69)**

**CONTACT METALLIZATION**

Base and emitter: > 30,000 Å Aluminum  
Collector: Gold  
(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

**MOLY PEDESTAL**

Size: .140" Diameter (3.56mm)  
Thickness: .010" (0.25mm)

**BeO PEDESTAL**

Size: .142" x .178" (3.61mm x 4.52mm)  
Thickness: .023" (0.58mm)

**ASSEMBLY RECOMMENDATIONS**

It is advisable that:

- a) the chip be eutectically mounted with gold silicon preform 98/2%.
- b) 8 mil (0.203mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

**TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C**

The following typical electrical characteristics apply for a completely finished component employing the chip number 269 in a TO-66 or equivalent case:

V <sub>CEO</sub>	V <sub>CE(s)</sub> @	I <sub>C</sub>	I <sub>B</sub>	h <sub>FE</sub> @	I <sub>C</sub>	V <sub>CE</sub>
> 60V	< 0.35V	0.5A	50mA	> 15	2A	5V
> 80V	< 0.35V	0.5A	50mA	> 15	2A	5V
> 100V	< 0.35V	0.5A	50mA	> 15	2A	5V
* > 150V	< 0.35V	0.5A	50mA	> 5	2A	5V
* > 200V	< 0.35V	0.5A	50mA	> 5	2A	5V

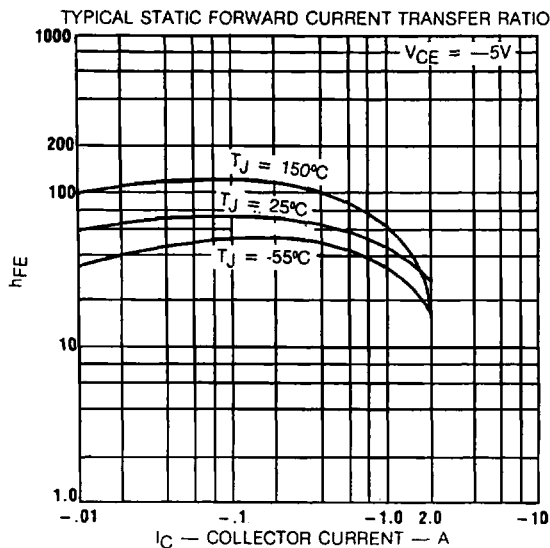
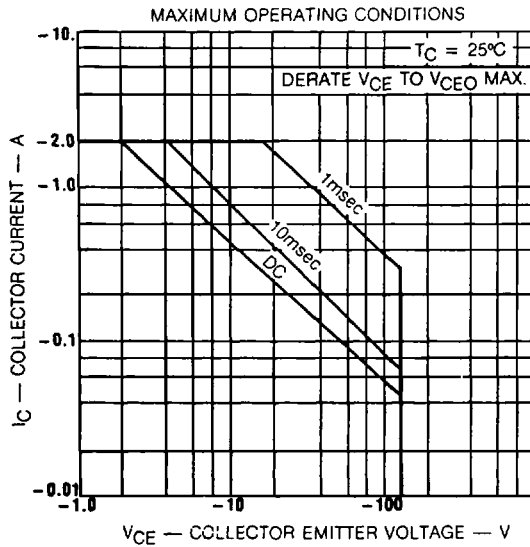
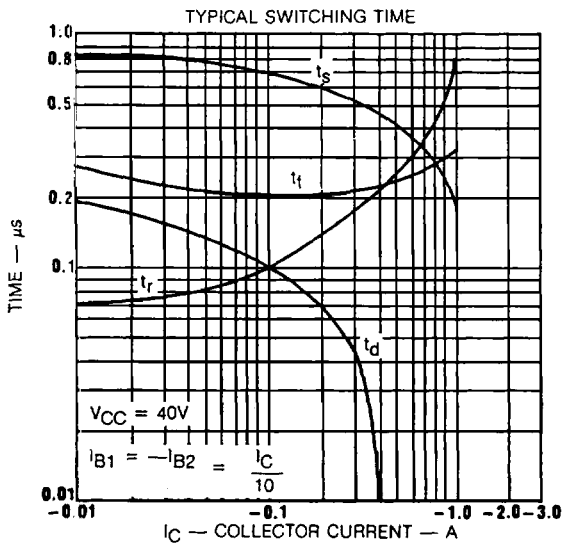
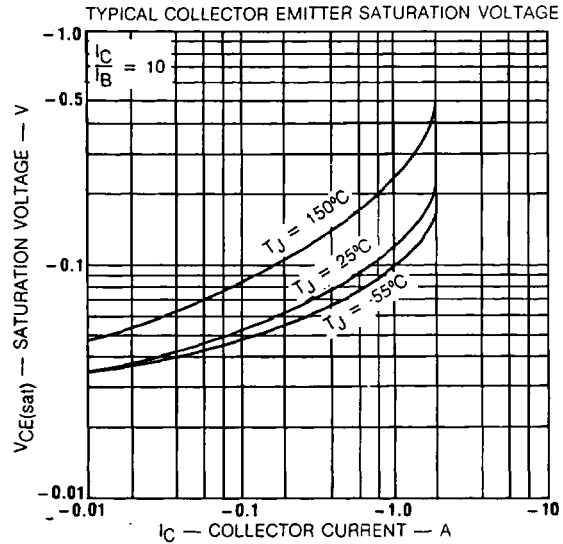
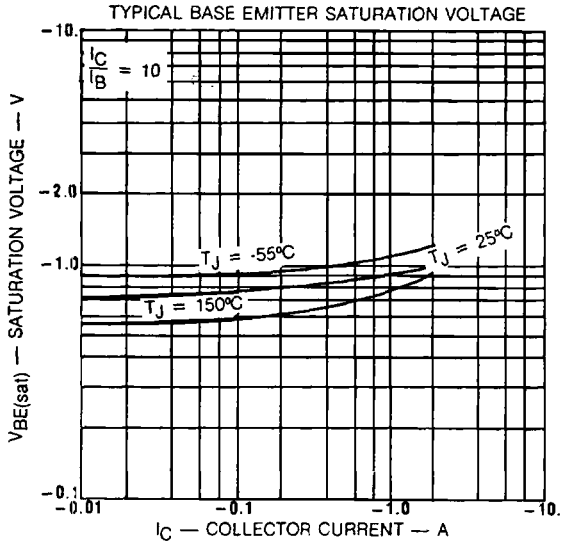
V <sub>CEO</sub>	V <sub>CEX</sub>	V <sub>EBO</sub>	f <sub>T</sub>	C <sub>OBO</sub>	θ <sub>JC</sub>
> 60V	70V	> 5V	40MHz	< 60pF	< 25°C/W
> 80V	90V	> 5V	40MHz	< 60pF	< 25°C/W
> 100V	110V	> 5V	40MHz	< 60pF	< 25°C/W
> 150V	160V	> 5V	40MHz	< 60pF	< 25°C/W
> 200V	210V	> 5V	40MHz	< 60pF	< 25°C/W

TYPICAL DEVICE TYPES: JAN2N3740, JAN2N3741, SDT69601 - SDT69613, SDT69501 - SDT69513

\*h<sub>FE</sub> available at I<sub>C</sub> = 500mA, V<sub>CE</sub> = 5V, > 20

\*\*The respective NPN complement is chip number 191.

MEDIUM TO HIGH VOLTAGE, FAST SWITCHING  
CHIP TYPE 269



**NOTE:**  
PERFORMANCE CURVES  
REPRESENT LOW TO  
MIDDLE CEO VOLTAGE  
RANGE OF THIS PRODUCT